

**AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions, and listings of claims in the application.

**LISTING OF CLAIMS:**

1-9. (Canceled).

10. (Currently amended) A semiconductor component comprising:

at least one first vertical power component ~~(5,9)~~ extending from a front side to a back side of a silicon substrate ~~(1)~~; and

at least one lateral, active component ~~(6)~~ and ~~optionally at least one second vertical power component (10)~~, between which at least one trench ~~(2)~~ filled with an insulation ~~(4)~~ is placed, said at least one trench ~~(2)~~ extending from said front side to said back side of said silicon substrate ~~(1)~~,

wherein said insulation ~~(4)~~ comprises at least partly one dielectric and wherein said at least one vertical power component ~~(5,9)~~ and said at least one lateral, active component ~~(6)~~ are designed approximately ring-shaped and/or disk-shaped and are arranged eccentrically or concentrically around a common point of reference on a said silicon substrate ~~(1)~~.

11. (Currently amended) A semiconductor component according to claim 10, wherein said at least one power component ~~(5,9)~~ is an IGBT, a PMOS and/or a diode.

12. (Currently amended) A semiconductor component according to claim 10, wherein said at least one power component ~~(5,9)~~ is suited for voltages of up to 1700 V.

13. (Currently amended) A semiconductor component according to claim 10, wherein said insulation (4) is composed of a combination of insulating, semiconducting and/or conducting materials.

14. (Currently amended) A semiconductor component according to claim 10, wherein said insulation (4) is composed of a combination of a dielectric and polysilicon.

15. (Currently amended) A semiconductor component according to claim 10, wherein said first vertical power component (5,9) and/or said at least one lateral, active component (6) is completely encompassed by at least one filled trench (2) and/or said at least one second vertical power component (10).

16. (Currently amended) A semiconductor component according to claim 10, wherein said at least one lateral, active component (6) is placed in a doped trough.

17. (Currently amended) A semiconductor component according to claim 10, wherein a dielectric (13) is applied on said back side of said substrate (1).

18. (Currently amended) A semiconductor component according to claim 17, wherein said dielectric (13) is provided with openings through which said power components (5,9,10) are contactable.

19. (New) A semiconductor component according to claim 10 comprising:

at least one second vertical power component extending from said front side to said back side of said silicon substrate, separated from said first vertical power component by a second trench filled with an insulation, said second trench extending from said front side to said back side of said silicon substrate,

wherein said insulation comprises at least partly one dielectric and

wherein said at least one second vertical power component is designed approximately ring-shaped and/or disk-shaped and is arranged eccentrically or concentrically around said common point of reference on said silicon substrate.